



## **60V N-Channel Enhancement Mode MOSFET**

Voltage

60 V

Current

40 A

#### **Features**

- $R_{DS(ON)}$ ,  $V_{GS}@10V$ , $I_D@15A<21m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}$ @4.5V, $I_{D}$ @8A<24 $m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

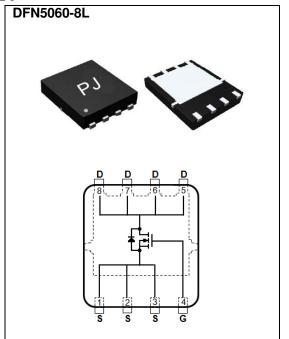
### **Mechanical Data**

• Case: DFN5060-8L Package

• Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0028 ounces, 0.08 grams

• Marking: Q5466A



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		$V_{DS}$	60	V	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V	
Continuous Drain Current	T <sub>C</sub> =25°C	I <sub>D</sub>	40	А	
	T <sub>C</sub> =100°C		25		
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	160		
Power Dissipation	T <sub>C</sub> =25°C	Po	83	W	
	T <sub>C</sub> =100°C		33		
Continuous Drain Current	T <sub>A</sub> =25°C	I <sub>D</sub>	6.5	Α	
	T <sub>A</sub> =70°C		5	Α	
Power Dissipation	T <sub>A</sub> =25°C	D-	2.0	W	
Power Dissipation	T <sub>A</sub> =70°C	Po	1.3		
Single Pulse Avalanche Energy (Note 6)		E <sub>AS</sub>	42	mJ	
Operating Junction and Storage Temperature Range		$T_{J}$ , $T_{STG}$	-55~150	°C	
Typical Thermal Resistance <sup>(Note 4,5)</sup>	Junction to Case	$R_{ heta JC}$	1.5	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

Limited only By Maximum Junction Temperature





## **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$V_{GS}=0V,I_D=250uA$	60	1	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250$ uA	1.0	1.73	2.5	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V,I <sub>D</sub> =15A	-	18	21	mΩ
		$V_{GS}$ =4.5V, $I_D$ =8A	-	21	24	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}$ =60V, $V_{GS}$ =0V	-	-	1.0	uA
Gate-Source Leakage Current	$I_{GSS}$	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)			_			
Total Gate Charge	$Q_g$	V <sub>DS</sub> =30V, I <sub>D</sub> =15A, V <sub>GS</sub> =10V <sup>(Note 1,2)</sup>	-	28	-	nC
Gate-Source Charge	$Q_gs$		-	3.5	-	
Gate-Drain Charge	$Q_{gd}$		-	6.5	-	
Input Capacitance	Ciss	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, f=1.0MHZ	_	1680	-	pF
Output Capacitance	Coss		_	115	-	
Reverse Transfer Capacitance	Crss	I=1.0WII IZ	-	85	-	
Turn-On Delay Time	td <sub>(on)</sub>	V 20V I 1A	-	7.2	-	
Turn-On Rise Time	t <sub>r</sub>	$V_{DD}$ =30V, $I_{D}$ =1A, $V_{GS}$ =10V, $R_{G}$ =6 $\Omega$ (Note 1,2)	-	38	-	ns
Turn-Off Delay Time	td <sub>(off)</sub>		-	34	-	
Turn-Off Fall Time	t <sub>f</sub>		-	8.2	-	
Drain-Source Diode			_			
Maximum Continuous Drain-Source	l.				40	Α
Diode Forward Current	I <sub>S</sub>		_	-	40	^
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A,V <sub>GS</sub> =0V	-	0.7	1.0	V

#### NOTES:

- 1. Pulse width < 300us, Duty cycle < 2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH,  $I_{AS}$ =29A,  $V_{DD}$ =25V,  $V_{GS}$ =10V
- 7. Guaranteed by design, not subject to production testing.





### TYPICAL CHARACTERISTIC CURVES

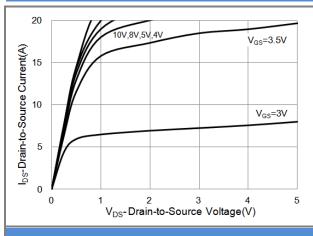


Fig.1 Output Characteristics

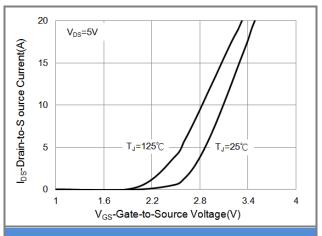


Fig.2 Transfer Characteristics

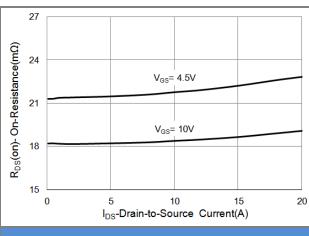


Fig.3 On-Resistance vs. Drain Current

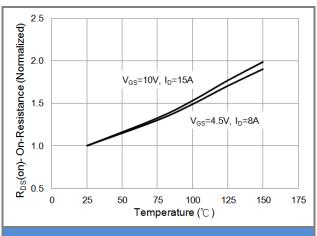
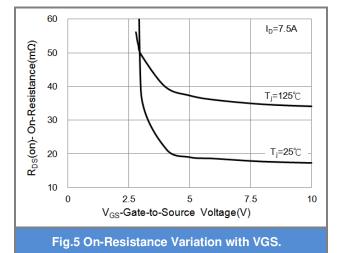


Fig.4 On-Resistance vs. Junction temperature



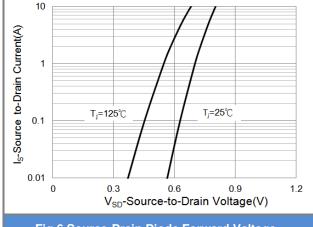


Fig.6 Source-Drain Diode Forward Voltage





### TYPICAL CHARACTERISTIC CURVES

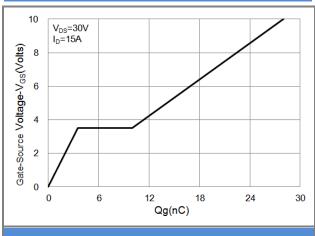


Fig.7 Gate-Charge Characteristics

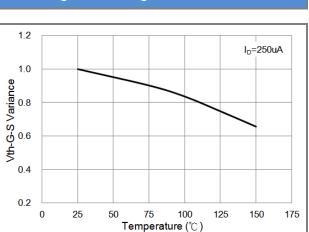
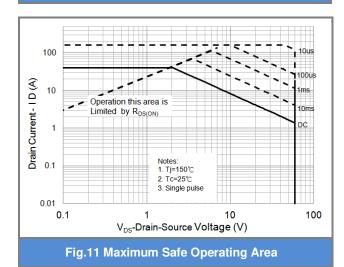


Fig.9 Threshold Voltage Variation with Temperature



BVDSS-Breakdown Voltage (Normalized) 1.1 1.0 0.9 8.0 100 125 175 0 25 75 150 Temperature (°€)

I<sub>D</sub>=250uA

Fig.8 Breakdown Voltage Variation vs. Temperature

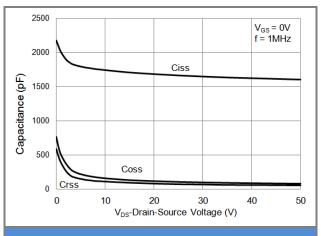


Fig.10 Capacitance vs. Drain-Source Voltage





### **TYPICAL CHARACTERISTIC CURVES**

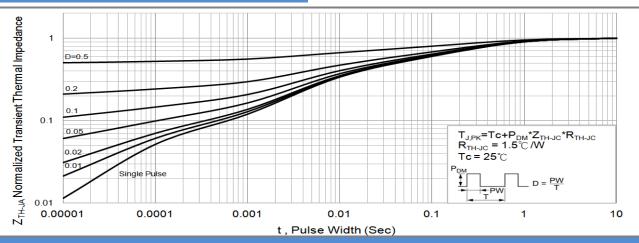


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

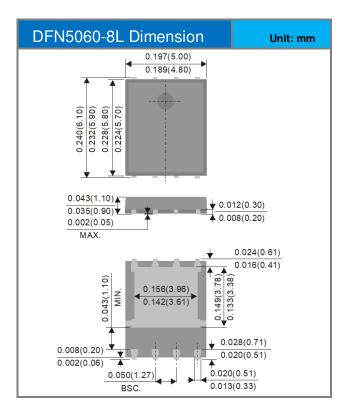


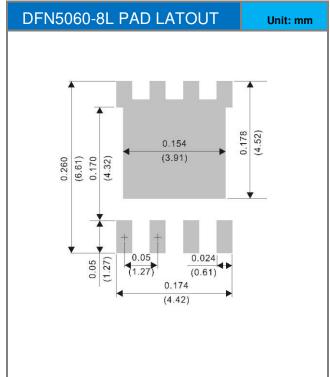


### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Packing type Marking	
PJQ5466A_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5466A	Halogen free

### **Packaging Information & Mounting Pad Layout**









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